

## RS2A-RS2M FAST RECOVERY RECTIFIERS

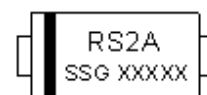
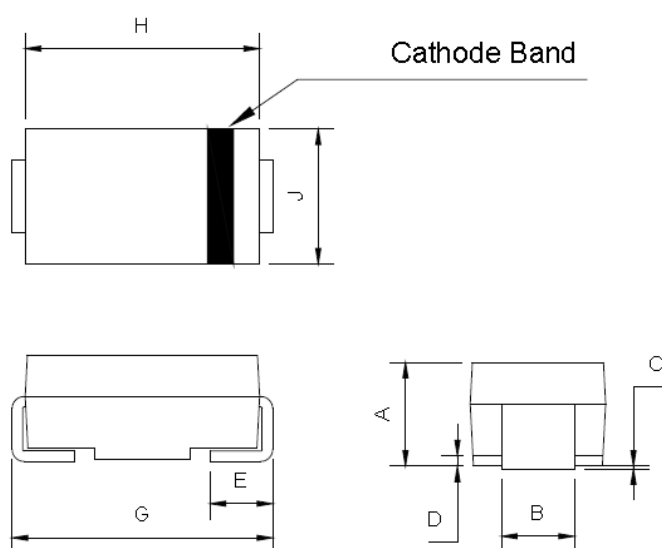
### Surface Mount - 2A

**Features:**

- Fast switching for high efficiency
- Low leakage current
- High forward surge capability
- Solder dip 260 °C, 40 s
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

**Mechanical Data:**

- Case: SMB molded plastic body
- Terminals: Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 0.09 grams


**RS2A**
**Mechanical Dimensions: In mm / Inches**


DIMENSIONS					
DIM	INCHES		MM		NOTE
	NMI	MAX	NMI	MAX	
A	0.083	0.096	2.13	2.44	
B	0.075	0.083	1.91	2.11	
C	0.002	0.008	0.051	0.203	
D	—	0.02	—	0.51	
E	0.030	0.060	0.76	1.52	
G	0.150	0.220	4.80	5.59	
H	0.160	0.185	4.06	4.70	
J	0.130	0.155	3.30	3.94	

**SMB**
**MARKING, MOLDING RESIN**

Marking for RS2A/B/C/D/G/J/M, 1<sup>st</sup> row RS2A/B/C/D/G/J/M, 2<sup>nd</sup> row SSG YYWWL

Where YY is the manufacture year

WW is the manufacture week code

L is the wafer's Lot Number



## RS2A-RS2M

Technical Data  
Data Sheet N1692, Rev. -

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### Ordering Information:

Device	Package	Shipping
RS2A-RS2M	SMB (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

### Maximum Ratings and Electrical Characteristics

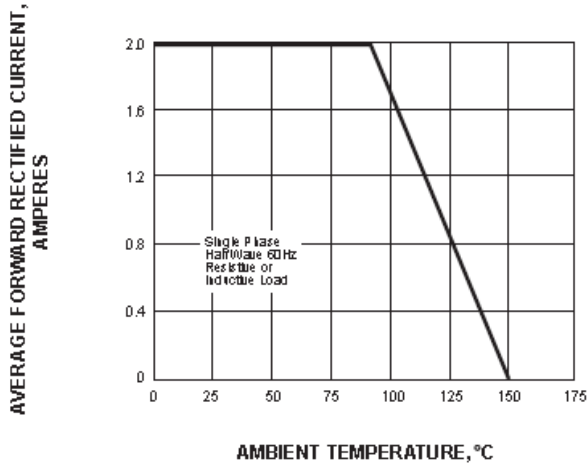
Rating at 25°C ambient temperature unless otherwise specified

Single Phase half wave 60Hz, resistive or inductive load. For capacitive load current derate by 20%.

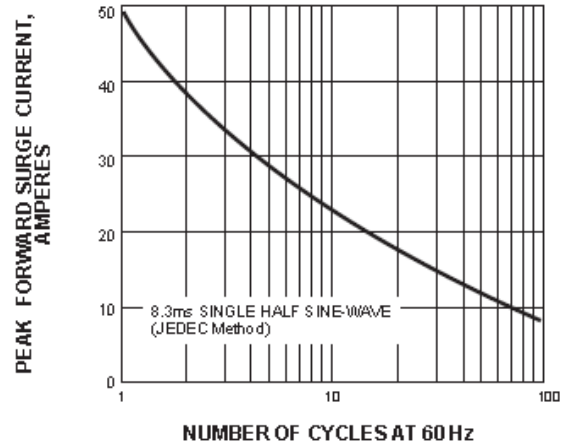
Characteristic	Symbol	RS2A	RS2B	RS2D	RS2G	RS2J	RS2K	RS2M	Units
Maximum repetitive peak reverse voltage	$V_{RRM}$	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	560	700	
Maximum average forward rectified current at $T_A = 90^\circ\text{C}$	$I_{(AV)}$	2.0							V
Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	$I_{FSM}$	50.0							A
Maximum instantaneous forward voltage at 2.0A	$V_F$	1.3							V
Maximum DC reverse current at rated DC blocking voltage $T_A = 25^\circ\text{C}$ $T_A = 100^\circ\text{C}$	$I_R$	5.0 50.0							$\mu\text{A}$
Maximum Reverse Recovery Time (Note 1)	$T_{rr}$	150			250	500			ns
Typical junction capacitance (Note 2)	$C_J$	50.0							pF
Typical thermal resistance (Note 3)	$R_{\theta JA}$	55.0							$^\circ\text{C}/\text{W}$
Operating junction and storage temperature range	$T_J, T_{STG}$	-65 to +150							$^\circ\text{C}$

- Note:**
1. Measured with  $I_F=0.5\text{A}$ ,  $I_R=1.0\text{A}$ ,  $I_{rr}=0.25\text{A}$ ,
  2. Measured at 1.0 MHz and applied reverse voltage of 4.0 VDC
  3. Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C.B. mounted

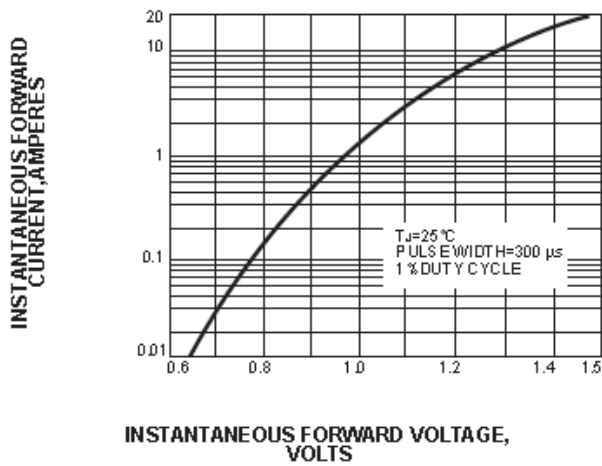
**FIG.1-FORWARD CURRENT DERATING CURVE**



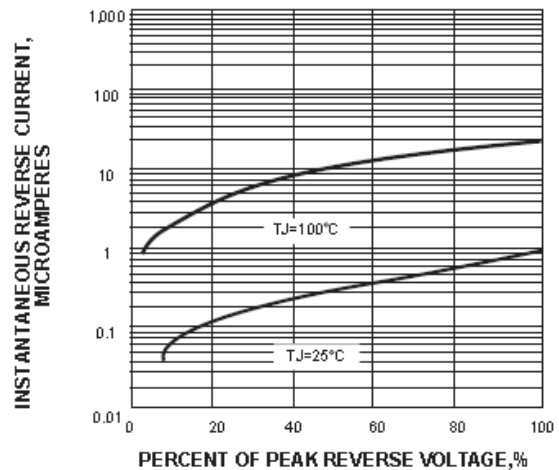
**FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT**



**FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS**



**FIG.4-TYPICAL REVERSE CHARACTERISTICS**





**RS2A-RS2M**

**Technical Data**  
**Data Sheet N1692, Rev. -**

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